

RFMW introduces 35W GaN transistor from TriQuint Semiconductor



RFMW, Ltd. announces design and sales support for TriQuint Semiconductor's [T1G4003532-FL](#) [1], DC - 3.5GHz GaN transistor offering up to 37W P3dB. Gain at P3dB is >13dB requiring half the power from a driver stage compared to some competitors. Linear gain is >16dB. The T1G4003532-FL uses a 32V supply and only 150mA of current. Overall efficiency is >53%. The -FL flange package offers low thermal resistance and is easily bolted down. Also available is an earless package in the [T1G4003532-FS](#) [2]. Both transistors are ideal for military and civilian radar, jammers and communications systems where high gain and high efficiency are required. The T1G4003532-FL is available from stock at RFMW, Ltd.

[T1G4003532-FL](#) [1]: Flanged Package, 35W, 32V, DC-3.5GHz GaN RF Power Transistor

[T1G4003532-FS](#) [2]: Earless Package, 35W, 32V, DC-3.5GHz GaN RF Power Transistor

www.rfmw.com [3]

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Links:

[1] <http://www.rfmw.com/ProductDetail/T1G4003532FL-TriQuint-Semiconductor-Inc/460141/>

[2] <http://www.rfmw.com/ProductDetail/T1G4003532FS-TriQuint-Semiconductor-Inc/460140/>

[3] <http://www.rfmw.com>